FCI-InGaAs-XXX-CCER

High Speed InGaAs Photodiodes Mounted on Cavity Ceramic Packages

FCI-InGaAs-XXX-CCER with active area sizes of 75µm, 120µm, 300µm, 400µm and 500µm are part of OSI Optoelectronics's high speed IR sensitive photodiodes mounted on gull wing ceramic substrates with glass windows. These devices have a glass window attached to the ceramic where fibers can be directly epoxy mounted onto. The chips can be epoxy or eutectic mounted onto the ceramic substrate. These devices can be provided with custom AR coated windows.

APPLICATIONS

- High Speed Optical Communications
- Gigabit Ethernet/Fibre Channel
- SONET / SDH, ATM
- Diode Laser Monitoring
- Instrumentation

FEATURES

- Low Noise
- High Speed
- 900nm to 1700nm





• High Responsivity

- Spectral Range
- Distributor



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Notes:

• All units in millimeters.

• All devices are mounted with low out gassing conductive epoxy with tolerance of ±25µm.

Eutectic mounting is also available upon request.

Absolute Maximum Ratings											
PARAMETERS	SYMBOL	MIN	МАХ	UNITS							
Storage Temperature	T _{stg}	-40	+85	°C							
Operating Temperature	T _{op}	0	+70	°C							
Soldering Temperature	T _{sld}		+260	°C							

Electro-Optical Characteristics T _A =23°C																		
PARAMETERS	SYMBOL	CONDITIONS	FCI-InGaAs-75CCER		FCI-InGaAs-120CCER		FCI-InGaAs-300CCER		FCI-InGaAs-400CCER			FCI-InGaAs-500CCEF			UNITE			
			MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	UNITS
Active Area Diameter	AA_{ϕ}			75			120			300			400			500		μm
Responsivity	P	λ=1310nm	0.80	0.90		0.80	0.90		0.80	0.90		0.80	0.90		0.80	0.90		A/W
	Γ _λ	λ=1550nm	0.90	0.95		0.90	0.95		0.90	0.95		0.90	0.95		0.90	0.95		
Capacitance	Cj	$V_{R} = 5.0V$		0.65			1.0			10.0			14.0			20.0		pF
Dark Current	I _d	$V_{R} = 5.0V$		0.03	2		0.05	2		0.30	5		0.40	5		0.50	20	nA
Rise Time/ Fall Time	t _r /t _f	$V_R = 5.0V,$ $R_L = 50\Omega$ 10% to 90%			0.20			0.30			1.5			3.0			10.0	ns
Max. Reverse Voltage					20			20			15			15			15	v
Max. Reverse Current					1			2			2			2			2	mA
Max. Forward Current					5			5			8			8			8	mA
NEP				3.44E- 15			4.50E- 15			6.28E- 15			7.69E- 15			8.42E- 15		W/√Hz